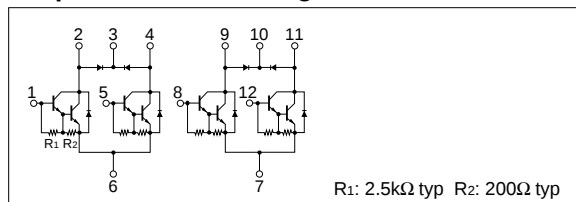


Absolute maximum ratings

(Ta=25°C)

Symbol	Ratings	Unit
V _{CB0}	120	V
V _{CEO}	120	V
V _{EBO}	6	V
I _C	5	A
I _{CP}	8 (PW≤1ms, Du≤50%)	A
I _B	0.5	A
I _F	5 (PW≤0.5ms, Du≤25%)	A
I _{FSM}	8 (PW≤10ms, single)	A
V _R	120	V
P _T	5 (Ta=25°C) 25 (Tc=25°C)	W
V _{ISO}	1000 (Between fin and lead pin, AC)	V _{rms}
T _J	150	°C
T _{stg}	-40 to +150	°C
θ _{J-C}	5	°C/W

Equivalent circuit diagram



Electrical characteristics

(Ta=25°C)

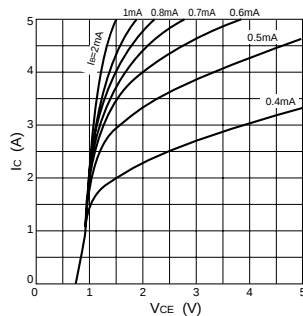
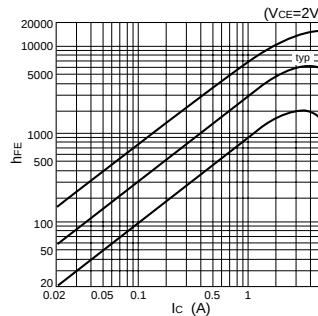
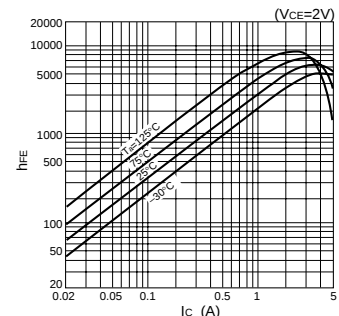
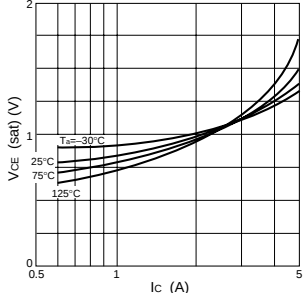
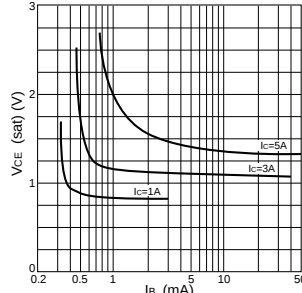
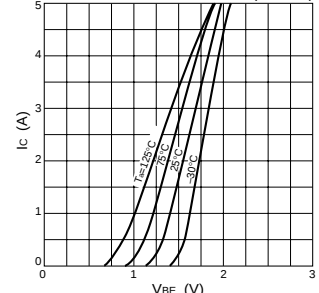
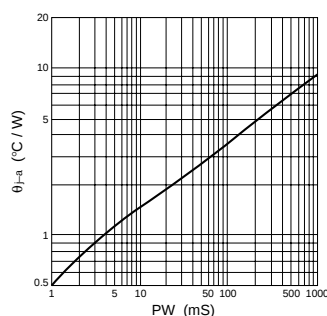
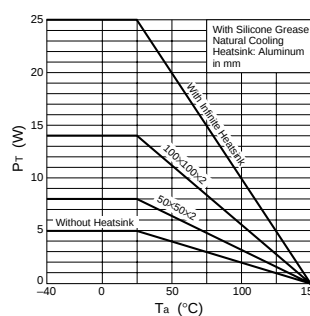
Symbol	Specification			Unit	Conditions
	min	typ	max		
I _{CB0}			10	μA	V _{CB} =120V
I _{EBO}			10	mA	V _{EB} =6V
V _{CEO}	120			V	I _C =25mA
h _{FE}	2000	5000	15000		V _{CE} =2V, I _C =3A
V _{CE(sat)}		1.0	1.5	V	I _C =3A, I _B =3mA
V _{BE(sat)}		1.6	2.0	V	
t _{on}		0.5		μs	V _{CC} ÷30V, I _C =3A, I _{B1} =-I _{B2} =3mA
t _{stg}		5.5		μs	
t _f		1.5		μs	

Diode for flyback voltage absorption

(Ta=25°C)

Symbol	Specification			Unit	Conditions
	min	typ	max		
V _R	120			V	I _R =10μA
V _F			1.2	V	I _F =1A
I _R			10	μA	V _R =120V
t _{rr}		100		ns	I _F =±100mA

Characteristic curves

I_C-V_{CE} Characteristics (Typical)h_{FE}-I_C Characteristics (Typical)h_{FE}-I_C Temperature Characteristics (Typical)V_{CE(sat)}-I_C Temperature Characteristics (Typical)(I_C / I_B=1000)V_{CE(sat)}-I_B Characteristics (Typical)I_C-V_{BE} Temperature Characteristics (Typical)(V_{CE}=2V)θ_{J-a}-PW CharacteristicsP_T-T_a Characteristics

Safe Operating Area (SOA)

